PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Attorney Docket No.: **040090.02**

Date: **July 10, 2001**

Customer Number: 25944

BOX PATENT APPLICATION

CONTINUING APPLICATION TRANSMITTAL
RULE 1.53(b)

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Transmitted herewith for filing under 37 C.F.R. §1.53(b) is a

☐ Continuation ☒ Divisional ☐ Continuation-in-Part

application of prior pending Application No. **09/325,567**, filed **June 4, 1999**,

For (Title): **THIN FILM DEVICE PROVIDED WITH COATING FILM, LIQUID CRYSTAL PANEL AND ELECTRONIC DEVICE, AND METHOD FOR MAKING THE THIN FILM DEVICE**

By (Inventors): **Ichio YUDASAKA, Tatsuya SHIMODA, Sadao KANBE and Wakao MIYAZAWA**

1. ☐ A Declaration and Power of Attorney is attached. The attached Declaration and Power of Attorney is:
   - ☐ a. A copy of the Declaration and Power of Attorney from the parent application. (Used with the same or fewer inventors and (a) a copy of the prior application or (b) a revised, reformatted or edited version of the prior application that does not contain new matter.)
   - ☐ b. A new Declaration and Power of Attorney. (Used with the same, fewer or additional inventors and (a) a copy of the prior application, (b) a revised, reformatted or edited version of the prior application that does not contain new matter, or (c) a new specification.)
2. ☒ The filing fee is calculated below:

CLAIMS IN THE APPLICATION AFTER ENTRY OF ANY PRELIMINARY AMENDMENT NOTED BELOW

FOR:	NO. FILED	NO. EXTRA	SMALL ENTITY RATE	SMALL ENTITY FEE		OTHER THAN A SMALL ENTITY RATE	OTHER THAN A SMALL ENTITY FEE
BASIC FEE				$ 355	OR		$ 710
TOTAL CLAIMS	51 - 20	= *31	x 9 =	$	OR	x 18	$ 558
INDEP CLAIMS	5 - 3	= *2	x 40 =	$	OR	x 80	$ 160
☐ MULTIPLE DEPENDENT CLAIMS PRESENTED			+135 =	$	OR	+270	$ 0
			TOTAL	$	OR	TOTAL	$1428

* If the difference is less than zero, enter "0".

3. ☒ Check No. **120770** in the amount of **$1,428.00** to cover the filing fee is attached. The Director is hereby authorized to charge any other fees that may be required to complete this filing, or to credit any overpayment, to Deposit Account No. 15-0461. Two duplicate copies of this sheet are attached.
4. ☐ Cancel claims _____ of the application before calculating the filing fee. At least one independent claim is retained for filing purposes.

DEPOSIT ACCOUNT USE AUTHORIZATION
Please grant any extension necessary for entry;
Charge any fee due to our Deposit Account No. 15-0461

5. ☒ Amend the specification by inserting before the first line the sentence:
--This is a ☐ Continuation ☒ Division ☐ Continuation-in-Part of Application No. **09/325,567** filed **June 4, 1999**, which is a **Rule 1.53(b) Continuation of U.S.S.N. 08/983,036**, which in turn is a **U.S. National Stage Application of PCT/JP97/01618**. The entire disclosure of the prior application(s) is hereby incorporated by reference herein in its entirety.--

6. ☒ Drawings (Fig(s). **1-44**) are attached.
☐ Use Figure for front page of Publication.

7. ☒ Priority of foreign application(s) No. **8-120653** filed **May 15, 1996** in **Japan**; **8-248071** filed **September 19, 1996** in **Japan**; **8-303387** filed **November 14, 1996** in **Japan** are claimed under 35 U.S.C. §119 and/or §365(b).
☐ The certified copy was filed in prior Application No. _____ on _____.
☐ A certified copy of the above foreign application(s) is filed herewith.

8. ☐ Priority of U.S. Provisional Application(s) No. _____ filed _____ is claimed under 35 U.S.C. §119.
☐ Amend the specification by inserting before the first line the sentence:
--This nonprovisional application claims the benefit of U.S. Provisional Application(s) No. _____ filed _____.--

9. ☒ The prior application is assigned of record to **Seiko Epson Corporation** recorded at Reel **9149**, Frame **0850**.

10. ☐ This application is filed by fewer than all the inventors named in the prior application (37 C.F.R §1.53(b)(1)). Delete the following inventor(s) named in the prior application:

_____ _____

_____ _____

11. ☒ A Preliminary Amendment is attached. Claims added by this Amendment are properly numbered consecutively beginning with the number next following the highest numbered claim in the application.

12. ☒ An Information Disclosure Statement is attached.

13. ☐ Small entity status:
☐ a. Entitlement to small entity status is asserted.
☐ b. Small entity status is no longer claimed.

14. ☐ Other: _____

15. ☐ This application is NOT to be published under 35 U.S.C. 112(b). The undersigned attorney or agent hereby certifies that the invention disclosed in this application has not been and will not be the subject of an application filed in another country, or under a multilateral international agreement, that requires publication at eighteen months after filing.

16. ☐ The power of attorney in the application is to James A. Oliff, Registration No. 27,075, William P. Berridge, Registration No. 30,024, Kirk M. Hudson, Registration No. 27,562, Thomas J. Pardini, Registration No. 30,411, Edward P. Walker, Registration No. 31,450, Robert A. Miller, Registration No. 32,771, Mario A. Costantino, Registration No. 33,565, Stephen J. Roe, Registration No. 34,463, Joel S. Armstrong, Registration No. 36,430, Christopher W. Brown, Registration No. 38,025, and/or Richard E. Rice, Registration No. 31,560.
☐ a. The power appears in the attached Declaration and Power of Attorney.
☐ b. Since the power does not appear in the attached Declaration and Power of Attorney, a substitute Power of Attorney is also attached.

17. ☒ Address all future communications to:

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Respectfully submitted,

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Registration No. 27,075

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JAO:EDM/gam

Count	Claim in '196 Patent	Claims in 09/901,126	Support in 09/901,126	Support in Priority Doc JP 8-120653
Count 3. A process of forming thin film field effect transistors comprising the steps of: forming a gate electrode on a substrate; forming a gate insulator over said gate electrode; forming a semiconducting layer on said insulator by ink-jet printing; and forming source and drain contacts on said semiconducting layer.	23. A process of forming thin film field effect transistors comprising the steps of: forming a gate electrode on a substrate; forming a gate insulator over said gate electrode; forming a polymer semiconducting layer on said insulator by ink-jet printing; and forming source and drain contacts on said semiconducting layer.	82. A process of forming thin film field effect transistors comprising the steps of: forming a gate electrode on a substrate; forming a gate insulator over said gate electrode; forming a polymer semiconducting layer on said insulator by ink-jet printing; and forming source and drain contacts on said semiconducting layer.	Fig. 38(B), P93, L1-4: reverse stagger-type TFT. Fig. 38(B), P93, L1-P94, L21: - insulating substrate 410 and protective underlayer 411. - gate electrode 415. - gate insulating film 413. - amorphous silicon film 417. - source/drain electrodes 431, 492. P94, L22, P95, L4: Semiconducting layer can be formed of a coating film as in the first embodiment. P41-42: using polymer silane having various plural monomer units as the material forming the conductive layer; P58, L5-9: using ink-jetting to deposit the material forming the conductive layer. Figs. 14-16; P56, L1-P59, L21: Ink-jet printing also, applicable to the silicon film forming the channel region (region 14C between 14S and 14D in Fig. 10). See P58, L5-9.	P24, ¶42 through page 26 ¶44 describes the TFT and its components (by reference to Figures 3 and 4, including an insulating substrate 401, a gate electrode 405, gate insulating film 404, semiconducting channel region 403, source contacts 403S, and drain contacts 403D), wherein the channel region is formed from polymer silane having various plural monomer units as the material forming the polymer semiconducting layer; P39, ¶39 describes using ink-jetting to form the channel and the insulating film.